

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

SCH1404 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		2.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	10	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=1.5A	1.8	3.0		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =1.5A, V _{GS} =10V		84	110	mΩ
	R _{DS} (on)2	I _D =1A, V _G S=4V		125	175	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		180		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		42		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		25		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		7.0		ns
Rise Time	t _r	See specified Test Circuit.		2.8		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		18.5		ns
Fall Time	tf	See specified Test Circuit.		4.4		ns

Marking: KD Continued on next page.

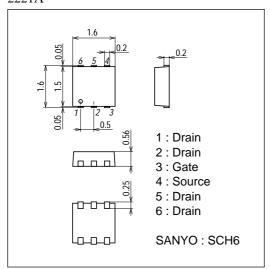
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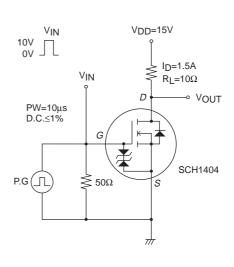
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =2.5A		4.9		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =2.5A		0.93		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =2.5A		0.63		nC
Diode Forward Voltage	VsD	IS=2.5A, VGS=0		0.85	1.2	V

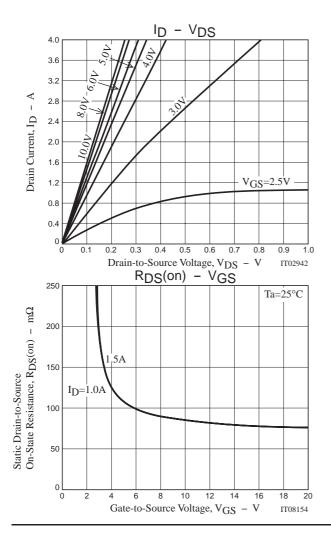
Package Dimensions

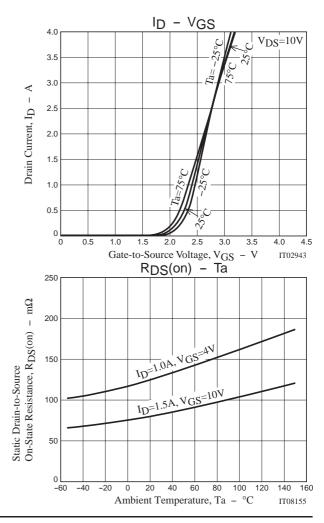
unit : mm 2221A

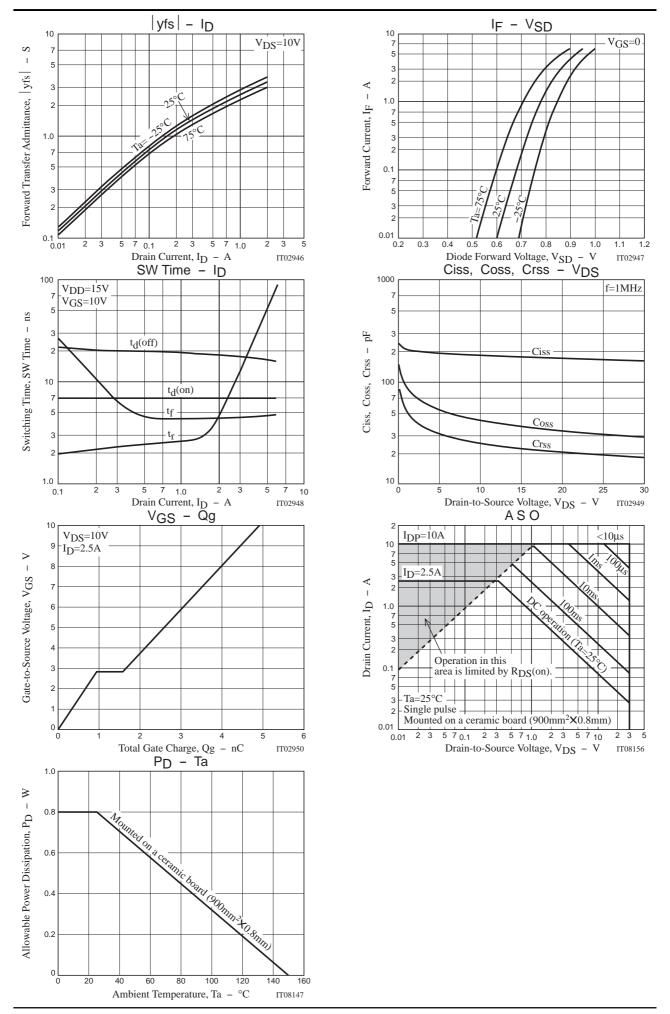


Switching Time Test Circuit









Note on usage: Since the SCH1404 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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